

REMARKS

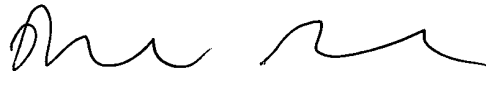
Claims 1 and 55 have been amended. Claims 1-18 and 53-62 are pending in the application. Consideration of the application as amended is requested.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) are captioned "**Version with markings to show changes made.**"

This application is believed to be in condition for allowance and action to that end is requested. The Examiner is requested to telephone the undersigned in the event that the next office action is one other than a Notice of Allowance. The undersigned is available during normal business hours (Pacific Time Zone).

Respectfully submitted,

Dated: Mar. 20, 2002 By: _____


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Reg. No. 36,138



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MAIL ROOM

Version with markings to show changes made.
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 10/082,594
Filing Date February 22, 2002
Inventor Alan R. Reinberg
Assignee Micron Technology, Inc.
Group Art Unit Unassigned
Examiner Unassigned
Attorney's Docket No. MI22-1952
Title: Methods of Forming Capacitors and Resultant Capacitor Structures

37 CFR §1.121(b)(1)(iii) AND 37 CFR §1.121(c)(1)(ii)
FILING REQUIREMENTS TO ACCOMPANY PRELIMINARY AMENDMENT

Deletions are bracketed, additions are underlined.

In the Claims

1. (Twice amended) A method of forming a capacitor comprising:

forming a capacitor storage node layer over a substrate, the capacitor storage node layer having an uppermost rim defining an opening into an interior volume; and

forming a cap by capping at least a portion of the rim within the interior volume by forming a material which is different from the capacitor storage node layer over the rim portion[, said material as received at least over the rim portion not functioning primarily as a capacitor dielectric material for the capacitor].

55. (Amended) A method of forming a capacitor comprising:

forming a capacitor storage node layer comprising roughened polysilicon over a substrate, the capacitor storage node layer having an uppermost rim defining an opening into an interior volume;

forming an insulative cap by capping at least a portion of the rim within the interior volume by forming a material which is different from the capacitor storage node layer over the rim portion[, said material as received at least over the rim portion not functioning primarily as a capacitor dielectric material for the capacitor]; and

after the capping of the rim, forming a capacitor dielectric region and a cell electrode layer over the capacitor storage node layer.

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